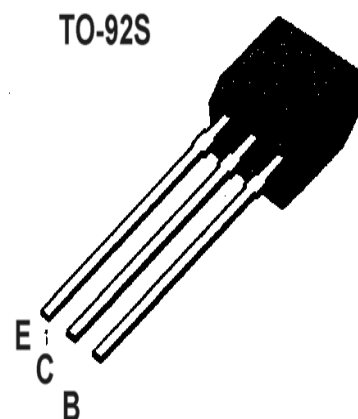


APPLICATION: For Driver Stage of AF Amplifier Applications.

MAXIMUM RATINGS (Ta=25℃)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-60	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-0.1	A
Base current	I _b	-0.02	A
Collector Power Dissipation	P _c	0.25	W
Junction Temperature	T _j	150	℃
Storage Temperature Range	T _{stg}	-55~150	℃



ELECTRICAL CHARACTERISTICS (Ta=25℃, R_G=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{cbo}	-60			V	I _c =-50uA	I _e =0	
Collector-Emitter Breakdown Voltage	BV _{ceo}	-50			V	I _c =-1mA	I _b =0	
Emitter-Base Breakdown Voltage	BV _{ebo}	-5			V	I _e =-50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			-0.1	uA	V _{cb} =-60V	I _e =0	
Collector-Emitter Saturation Voltage	I _{ebo}			-0.1	uA	V _{eb} =-5V	I _c =0	
Base-Emitter Voltage	V _{BE}	-0.58	-0.62	-0.68	V	V _{ce} =-6V	I _c =-1mA	
Collector-Emitter Saturation Voltage	V _{ce(sat)}		-0.18	-0.3	V	I _c =-100mA	I _b =-10mA	
DC Current Gain	h _{FE}	110		600	β	V _{ce} =-6V	I _c =-1mA	
Gain bandwidth product	f _T	50	180		MHz	V _{ce} =-6V	I _e =-1mA	
Common Base Output Capacitance	C _{ob}		5	6	pF	V _{cb} =-10V	I _E =0f=1MHz	
Noise Figure	NF		6	20	dB	V _{ce} =-6V	I _c =-0.3mAf=100Hz	

h_{FE} Classification And Marking

Print Mark	FR					
Classification	RF	JF	HF	FF	EF	KF
h _{FE}	110~180	135~220	170~270	200~320	250~400	300~600